

SS9015

Low Frequency, Low Noise Amplifier

- Complement to SS9014



TO-92
1. Emitter 2. Base 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-100	A
P_C	Collector Dissipation	450	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}, I_B = 0$	-45			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = -50\text{V}, I_E = 0$			-50	nA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = -5\text{V}, I_C = 0$			-50	nA
h_{FE}	DC Current Gain	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	60	200	600	
$V_{CE}(\text{sat})$	Collector-Base Saturation Voltage	$I_C = -100\text{mA}, I_B = -5\text{mA}$		-0.2	-0.7	
$V_{BE}(\text{sat})$	Base-Emitter Saturation Voltage	$I_C = -100\text{mA}, I_B = -5\text{mA}$		-0.82	-1.0	V
$V_{BE}(\text{on})$	Base-Emitter On Voltage	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	-0.6	-0.65	-0.75	V
C_{ob}	Output Capacitance	$V_{CB} = -10\text{V}, I_E = 0$ $f=1\text{MHz}$		4.5	7.0	pF
f_T	Current Gain Bandwidth Product	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$	100	190		MHz
NF	Noise Figure	$V_{CE} = -5\text{V}, I_C = -0.2\text{mA}$ $f=1\text{KHz}, R_S=1\text{K}\Omega$		0.7	10	dB

h_{FE} Classification

Classification	A	B	C
h_{FE}	60 ~ 150	100 ~ 300	200 ~ 600